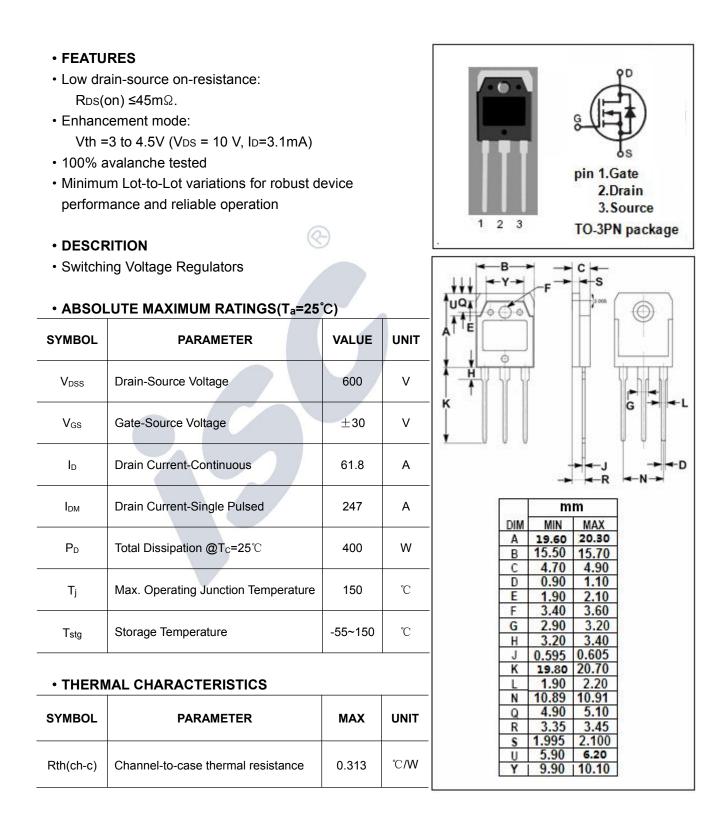


# isc N-Channel MOSFET Transistor

## TK62J60W5



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =10mA	600			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =10V; I <sub>D</sub> =3.1mA	3		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =30.9A			45	mΩ
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> = 0V			±1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V			100	uA
V <sub>SDF</sub>	Diode forward voltage	I <sub>DR</sub> =61.8A, V <sub>GS</sub> = 0 V			1.7	v



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